

**Supplementary Information**

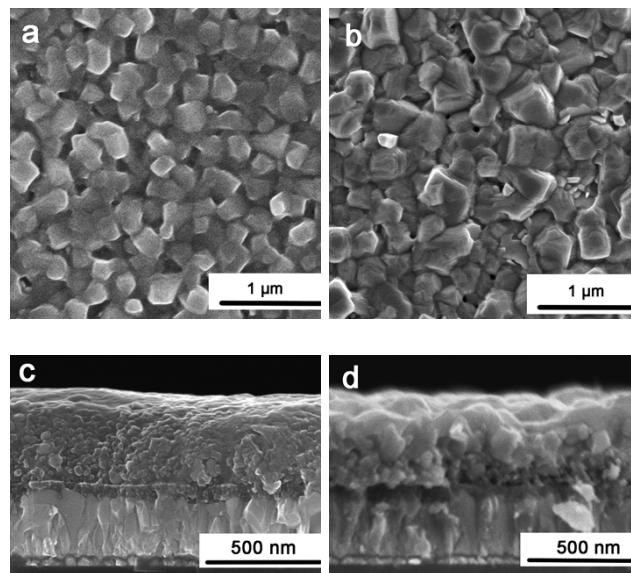
**Improved Light Absorption and Charge Transport for  
Perovskite Solar Cells with Rough Interfaces by  
Sequential Deposition**

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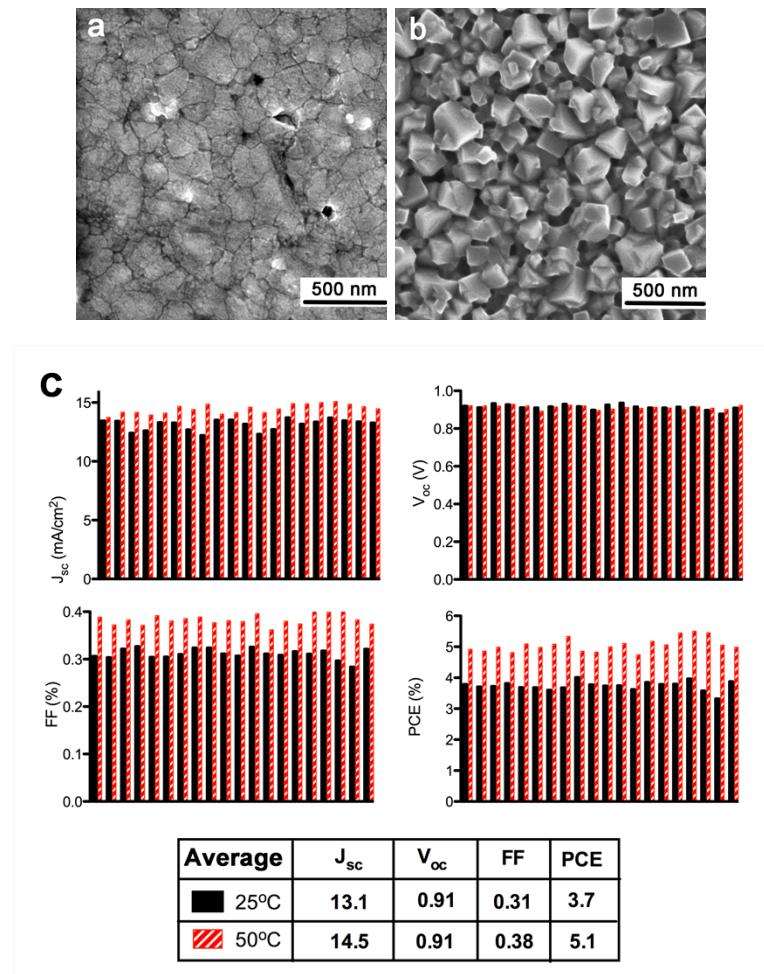
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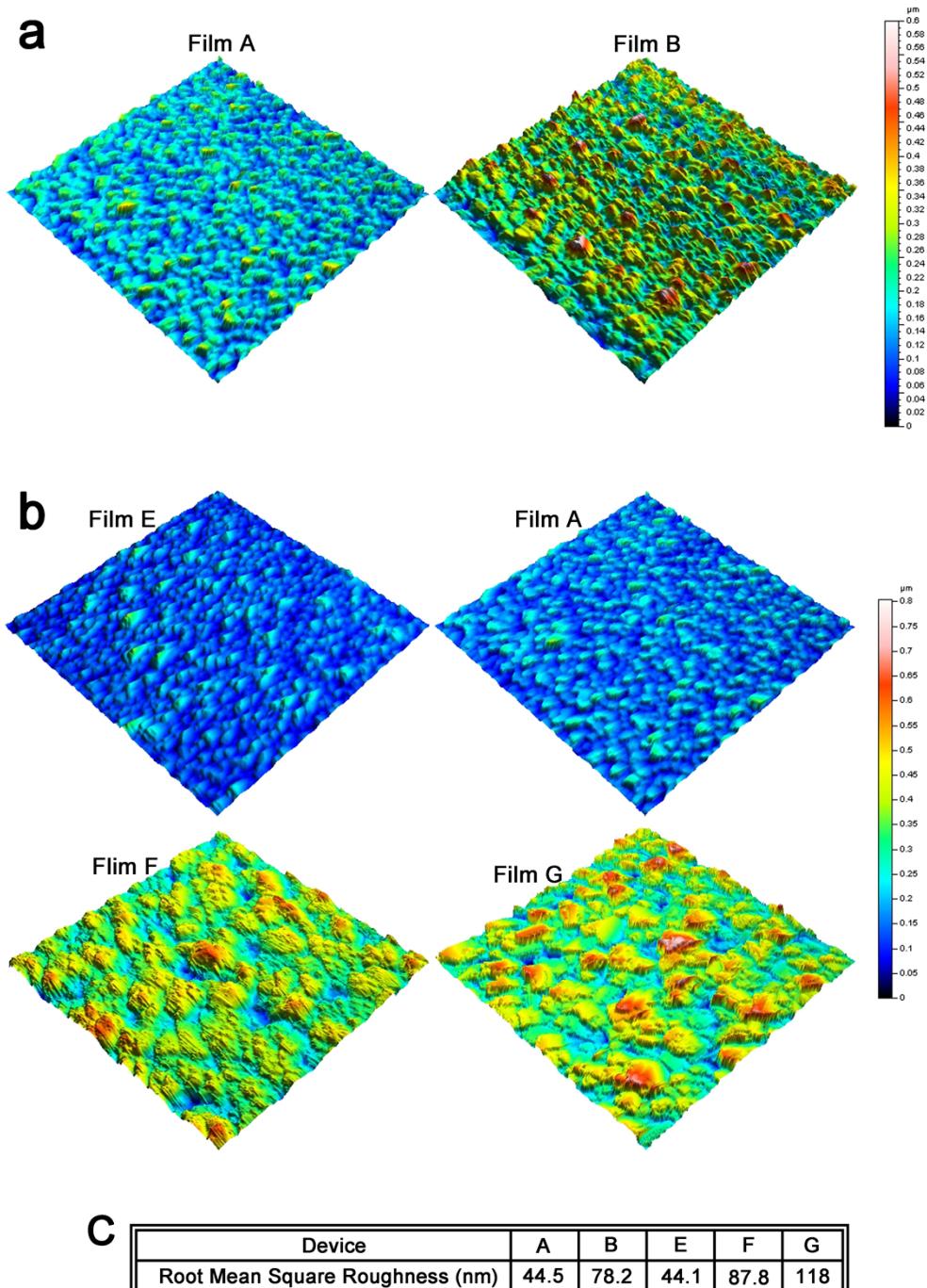
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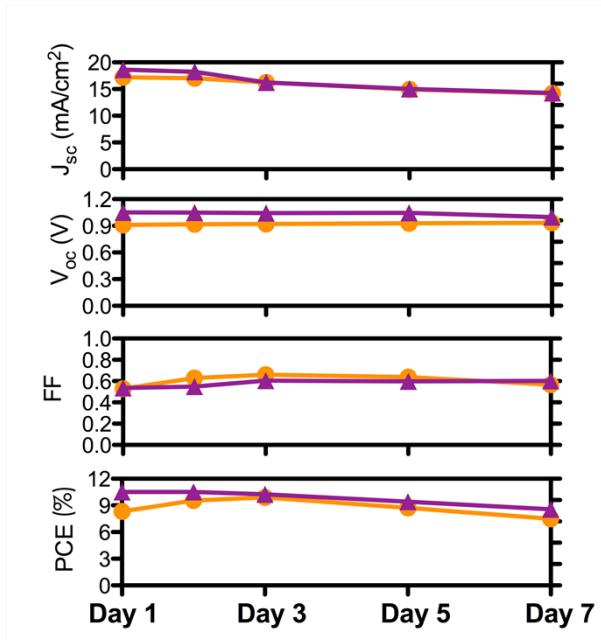
**Figure S1.** Top-view and cross-sectional SEM images of the  $\text{CH}_3\text{NH}_3\text{PbI}_{3-x}\text{Cl}_x$  ( $x \approx 0.5$ ) on top of the mesoporous  $\text{TiO}_2$  by reacting a) and c) at  $25^\circ\text{C}$ , b) and d) at  $50^\circ\text{C}$ .



**Figure S2.** Top-view SEM images of  $\text{CH}_3\text{NH}_3\text{PbI}_3$  on top of the compact  $\text{TiO}_2$  by reacting a) at  $25^\circ\text{C}$ , b) at  $50^\circ\text{C}$ . c) Histogram plots of device performance parameters and the average performance for 20 individual cells by different reaction temperature based on the structure: FTO/compact  $\text{TiO}_2/\text{CH}_3\text{NH}_3\text{PbI}_3/\text{spiro-MeOTAD}/\text{Ag}$ . The thickness of each layer is in accordance with devices including mesoporous  $\text{TiO}_2$ , without further optimizing.



**Figure S3.** 3D topographic images ( $10 \times 10 \mu\text{m}$ ) of a) Film A and B (scale bar=0.6  $\mu\text{m}$ ) and b) Film E, A, F and G (scale bar=0.8  $\mu\text{m}$ ) by tapping-mode atomic force microscopy. c) Surface roughness of the corresponding films.



**Figure S4.** Evolution of photovoltaic parameters under 100 mW cm<sup>-2</sup> simulated AM1.5G irradiation. Device B (orange) and Device D (purple) were stored in air at room temperature in the dark (humidity: 10%~40%) without encapsulation.

**Table S1. Photovoltaic parameters of a batch of twenty Device A-F measured under 100 mW cm<sup>-2</sup> simulated AM1.5G irradiation.**

Device A	$V_{oc}$ (V)	$J_{sc}$ (mA cm <sup>-2</sup> )	FF	PCE (%)	Device B	$V_{oc}$ (V)	$J_{sc}$ (mA cm <sup>-2</sup> )	FF	PCE (%)
1	0.94	14.0	0.54	7.2	1	0.93	16.0	0.52	7.7
2	0.91	15.1	0.53	7.2	2	0.93	16.1	0.52	7.7
3	0.91	15.1	0.57	7.8	3	0.92	16.0	0.53	7.8
4	0.91	15.9	0.57	8.3	4	0.93	16.1	0.52	7.7
5	0.91	15.3	0.55	7.6	5	0.90	16.5	0.52	7.7
6	0.92	14.6	0.55	7.4	6	0.92	16.1	0.53	7.8
7	0.90	16.0	0.54	7.8	7	0.92	16.4	0.52	7.9
8	0.91	14.4	0.54	7.2	8	0.95	16.6	0.55	8.7
9	0.92	15.8	0.51	7.4	9	0.92	16.0	0.53	7.9
10	0.91	15.4	0.52	7.3	10	0.91	16.7	0.52	7.9
11	0.91	16.0	0.56	8.2	11	0.91	16.5	0.52	7.8
12	0.90	15.7	0.55	7.8	12	0.91	16.8	0.52	8.0
13	0.91	15.9	0.54	7.7	13	0.90	16.7	0.52	7.8
14	0.91	15.9	0.55	8.0	14	0.92	16.4	0.53	8.0
15	0.91	15.2	0.59	8.1	15	0.94	15.7	0.52	7.7
16	0.91	15.6	0.60	8.5	16	0.92	16.6	0.53	8.2
17	0.91	15.3	0.52	7.3	17	0.91	16.6	0.53	8.0
18	0.91	14.7	0.54	7.3	18	0.94	16.2	0.56	8.4
19	0.93	15.1	0.56	7.8	19	0.93	15.9	0.53	7.8
20	0.93	15.2	0.50	7.1	20	0.93	15.8	0.53	7.8

<b>Average</b>	0.91	15.3	0.55	7.6	21	0.91	17.7	0.63	10.2
22	0.91	16.3	0.69	10.2					
23	0.94	18.1	0.59	10.0					
24	0.92	16.2	0.66	9.9					
25	0.92	17.1	0.61	9.6					
26	0.94	16.0	0.64	9.6					
27	0.89	16.8	0.63	9.4					
28	0.93	16.5	0.59	9.1					
29	0.91	17.0	0.57	8.8					
30	0.94	17.5	0.52	8.5					
31	0.94	17.3	0.52	8.4					
32	0.94	17.5	0.51	8.4					
33	0.91	17.2	0.53	8.3					
34	0.93	15.8	0.61	9.0					
35	0.93	15.7	0.63	9.1					
36	0.92	15.6	0.60	8.5					
37	0.91	15.9	0.57	8.3					
38	0.90	16.3	0.56	8.3					
39	0.91	16.1	0.56	8.1					
40	0.91	16.0	0.57	8.2					
<b>Average</b>	0.92	16.5	0.56	8.4					

Device C	V <sub>oc</sub> (V)	J <sub>sc</sub> (mA cm <sup>-2</sup> )	FF	PCE (%)	Device D	V <sub>oc</sub> (V)	J <sub>sc</sub> (mA cm <sup>-2</sup> )	FF	PCE (%)
1	0.97	15.4	0.58	8.6	1	0.96	16.8	0.53	8.6
2	0.97	15.3	0.55	8.2	2	1.05	18.7	0.54	10.5
3	1.00	15.5	0.57	8.8	3	0.94	17.6	0.52	8.6
4	0.96	15.7	0.55	8.3	4	0.97	17.7	0.55	9.5
5	0.98	15.3	0.56	8.3	5	1.05	18.2	0.55	10.5
6	0.97	15.2	0.54	7.9	6	1.00	18.2	0.59	10.8
7	0.99	15.1	0.57	8.5	7	0.99	19.0	0.56	10.5
8	1.01	15.1	0.60	9.2	8	1.00	15.6	0.57	9.2
9	0.99	15.6	0.57	8.9	9	1.00	15.5	0.57	8.8
10	0.97	16.2	0.57	8.9	10	1.04	15.4	0.58	9.3
11	0.96	16.0	0.56	8.6	11	0.96	18.1	0.55	9.5
12	0.96	15.2	0.56	8.2	12	0.96	17.7	0.56	9.5
13	0.97	15.5	0.58	8.7	13	0.95	17.2	0.55	9.0
14	0.97	15.3	0.57	8.5	14	0.97	16.9	0.55	9.0
15	0.96	15.5	0.57	8.5	15	0.96	16.7	0.53	8.4
16	0.98	15.1	0.58	8.5	16	0.96	17.1	0.54	8.9
17	1.02	15.3	0.57	8.9	17	0.96	16.0	0.56	8.7
18	0.96	15.5	0.56	8.3	18	0.96	16.7	0.56	9.0
19	0.95	15.8	0.57	8.5	19	0.93	18.2	0.55	9.3
20	0.95	15.9	0.55	8.3	20	0.98	18.0	0.56	9.8
<b>Average</b>	0.97	15.5	0.57	8.5	21	0.99	17.8	0.52	9.1
22	1.04	17.6	0.58	10.7					
23	1.04	16.3	0.61	10.2					
24	1.04	16.2	0.56	9.5					
25	0.97	15.9	0.60	9.2					
<b>Average</b>	0.99	17.2	0.56	9.5					

Device E	V <sub>oc</sub> (V)	J <sub>sc</sub> (mA cm <sup>-2</sup> )	FF	PCE (%)	Device F	V <sub>oc</sub> (V)	J <sub>sc</sub> (mA cm <sup>-2</sup> )	FF	PCE (%)
1	0.91	15.5	0.43	6.1	1	0.80	18.5	0.52	7.6
2	0.95	15.0	0.46	6.5	2	0.90	18.9	0.46	7.8
3	0.95	14.4	0.46	6.3	3	0.89	18.3	0.45	7.4
4	0.95	13.8	0.48	6.3	4	0.90	18.6	0.45	7.6
5	0.94	14.2	0.46	6.1	5	0.90	17.4	0.45	7.1
6	0.94	14.6	0.47	6.4	6	0.90	18.8	0.44	7.5
7	0.93	14.9	0.45	6.3	7	0.90	17.7	0.46	7.3
8	0.94	14.9	0.46	6.4	8	0.89	17.6	0.46	7.2
9	0.93	15.1	0.46	6.4	9	0.89	17.4	0.47	7.2
10	0.95	14.2	0.46	6.2	10	0.89	18.0	0.47	7.5
11	0.93	14.4	0.46	6.1	11	0.89	17.6	0.47	7.4
12	0.92	15.2	0.43	6.0	12	0.89	18.5	0.47	7.7

13	0.92	14.6	0.44	6.0	13	0.89	16.7	0.50	7.4
14	0.91	14.9	0.44	6.0	14	0.89	16.3	0.49	7.1
15	0.91	15.1	0.45	6.2	15	0.89	16.0	0.49	7.0
16	0.95	14.4	0.46	6.4	16	0.88	16.5	0.50	7.3
17	0.94	15.3	0.46	6.6	17	0.90	16.3	0.49	7.1
18	0.93	15.3	0.45	6.4	18	0.86	17.3	0.49	7.3
19	0.90	15.8	0.44	6.2	19	0.85	17.7	0.49	7.4
20	0.96	14.4	0.43	5.9	20	0.87	16.8	0.49	7.1
<b>Average</b>	0.93	14.8	0.45	6.2	<b>Average</b>	0.88	17.5	0.48	7.4

Device G	V <sub>oc</sub> (V)	J <sub>sc</sub> (mA cm <sup>-2</sup> )	FF	PCE (%)
1	0.82	16.2	0.44	5.8
2	0.77	17.2	0.51	6.8
3	0.75	15.8	0.53	6.3
4	0.73	16.2	0.52	6.2
5	0.73	15.6	0.51	5.8
6	0.72	14.7	0.48	5.0
7	0.71	15.4	0.49	5.3
8	0.72	16.4	0.49	5.8
9	0.71	17.0	0.49	6.0
10	0.70	16.5	0.48	5.6
11	0.82	16.2	0.43	5.8
12	0.72	15.6	0.51	5.7
13	0.80	17.1	0.45	6.2
14	0.77	15.5	0.43	5.1
15	0.70	15.5	0.48	5.3
16	0.69	15.3	0.48	5.1
17	0.75	14.5	0.50	5.4
18	0.74	15.6	0.50	5.8
19	0.74	15.6	0.48	5.5
20	0.73	15.1	0.52	5.8
<b>Average</b>	0.74	15.8	0.49	5.7